

General Purpose 0.5 μm N-Type GaAs MESFET Transistors

MA4TF50 Series

V3.00

Features

- Low Noise Figure
- High Associated Gain
- High Maximum Available Gain
- Designed for Battery Operation
- Useful to Ku-Band

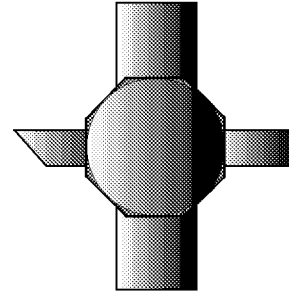
Description

The MA4TF50 is an n-type GaAs depletion mode Metal Semiconductor Field Effect Transistor (MESFET) series with a 0.5 micron gate length and a periphery of 300 microns. The device is available in the ceramic surface mount package, MA4TF5005, and in other hermetically sealed packages. It is also available as a chip, MA4TF5000, with the active region protected by a scratch resistant silicon nitride passivation layer.

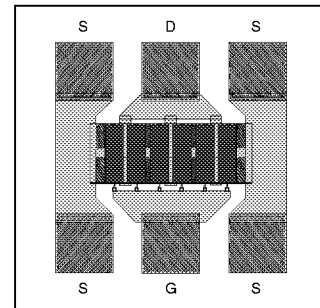
Applications

The MA4TF50 series is intended for low cost commercial applications including low noise microwave amplifiers up to X-band and oscillators up to Ku-band. The low voltage and low current biasing requirement is attractive for battery operation.

Case Styles



1105



Chip

Specifications Subject to Change Without Notice.

M/A-COM, Inc.

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MA4TF50 Series Maximum Ratings

(Case Temperature 25°C Unless Otherwise Noted)

Parameter	Symbol	Maximum
Total Power Dissipation of Chip	P_d	300 mW
Total Power Dissipation Ceramic Surface Mount Package	P_d	250 mW
Drain to Source Voltage	V_{DS}	10 V
Gate to Drain Voltage	V_{GDO}	-16 V
Gate to Source Voltage	V_{GSO}	-16 V
Drain Current	I_{DS}	125 mA
Gate Current	I_{GS}	1 mA
Storage Temperature Range	T_S	-65°C to +175°C
Channel Temperature	T_{CH}	+175°C
Lead Temperature	T_L	230°C for 10 seconds

MA4TF5005 (Ceramic Surface Mount Package) Electrical Specifications @ 25°C

Parameter	Condition	Symbol	Min	Typical	Max	Units
Saturated Drain to Source Current	$V_{DS} = 3\text{ V}$ $V_{GS} = 0\text{ V}$	I_{DSS}	30	50	—	mA
Pinch-off Voltage	$I_{DS} = 1\% I_{DSS}$	V_p	-0.5	-1.6	-2.5	V
Transconductance	$V_{DS} = 3\text{ V}$ $V_{GS} = 0\text{ V}$	G_m	—	45	—	mS
Gate-Drain Breakdown Voltage	$I_G = 10\ \mu\text{A}$	BV_{GDO}	-7	-14	—	V
Gate-Source Breakdown Voltage	$I_G = 10\ \mu\text{A}$	BV_{GSO}	-7	-14	—	V
Gate-Source Leakage Current	$V_{GS} = -5\text{ V}$	I_{GSO}	—	—	10	μA
Thermal Resistance (Channel to Ambient)	—	R_{TH}	—	200	—	°C/W
Maximum Frequency of Oscillation	$V_{DS} = 3\text{ V}$ $I_{DS} = 10\text{ mA}$	f_{MAX}	—	>60	—	GHz
Maximum Available Gain	$V_{DS} = 3\text{ V}$ $I_{DS} = 30\text{ mA}$ $f = 4\text{ GHz}$	MAG	—	16	—	dB
Optimum Noise Figure	$V_{DS} = 3\text{ V}$ $I_{DS} = 10\text{ mA}$ $f = 4\text{ GHz}$	NF_O	—	1.0	1.5	dB
Associated Gain	$V_{DS} = 3\text{ V}$ $I_{DS} = 10\text{ mA}$ $f = 4\text{ GHz}$	G_A	—	11.5	—	dB
Transducer Gain	$V_{DS} = 3\text{ V}$ $I_{DS} = 30\text{ mA}$ $f = 4\text{ GHz}$	$ S_{21} ^2$	4	8	—	dB
Power Output at 1 dB Compression	$V_{DS} = 3\text{ V}$ $I_{DS} = 30\text{ mA}$ $f = 4\text{ GHz}$	P_{1dB}	—	+16.0	—	dBm

Specifications Subject to Change Without Notice.

MA4TF5005

Typical Common Source Scattering Parameters in the Ceramic Surface Mount Package

 $V_{DS} = 3\text{ V}, I_{DS} = 10\text{ mA}$

Frequency (GHz)	S_{11E}		S_{21E}		S_{12E}		S_{22E}	
	Mag	Angle	Mag	Angle	Mag	Angle	Mag	Angle
0.50	1.02	-9.4	2.20	171.2	0.01	83.5	0.73	-6.2
1.00	1.02	-19.0	2.21	162.3	0.02	77.4	0.73	-12.5
1.50	1.01	-28.6	2.26	153.2	0.03	70.4	0.74	-19.5
2.00	0.97	-37.3	2.19	142.8	0.05	62.6	0.74	-25.5
2.50	0.95	-47.6	2.20	133.0	0.06	55.1	0.72	-32.3
3.00	0.93	-57.9	2.19	123.4	0.07	47.8	0.71	-39.1
3.50	0.91	-67.9	2.16	113.7	0.08	40.5	0.69	-45.9
4.00	0.88	-77.7	2.12	104.6	0.08	33.2	0.68	-52.0
4.50	0.86	-87.5	2.08	95.9	0.09	26.0	0.66	-57.8
5.00	0.83	-96.8	2.06	87.4	0.10	19.3	0.64	-63.3
5.50	0.81	-106.2	2.05	79.0	0.10	12.7	0.63	-69.0
6.00	0.78	-115.7	2.04	70.6	0.10	6.3	0.60	-74.7
6.50	0.75	-126.3	2.02	61.8	0.11	-0.3	0.58	-81.2
7.00	0.72	-136.8	2.00	52.7	0.11	-8.0	0.55	-87.6
7.50	0.70	-146.9	1.96	44.5	0.11	-13.6	0.53	-93.2
8.00	0.68	-157.1	1.94	36.4	0.11	-17.6	0.51	-99.1
8.50	0.68	-167.4	1.93	28.0	0.11	-20.9	0.50	-105.8
9.00	0.68	-177.8	1.90	19.5	0.11	-25.3	0.49	-113.4
9.50	0.67	172.1	1.86	11.2	0.11	-30.2	0.48	-120.8
10.00	0.67	163.2	1.82	3.3	0.11	-34.5	0.47	-128.1
10.50	0.67	153.6	1.78	-4.5	0.11	-38.9	0.46	-136.0
11.00	0.68	144.1	1.75	-12.6	0.11	-43.4	0.46	-143.8
11.50	0.68	134.5	1.70	-20.8	0.11	47.9	0.45	-152.1
12.00	0.69	125.4	1.66	-29.1	0.11	-52.0	0.44	-160.6
12.50	0.70	116.2	1.61	-37.4	0.10	-55.8	0.44	-169.9
13.00	0.70	107.7	1.55	-45.7	0.10	-59.1	0.43	-179.7
13.50	0.71	99.5	1.49	-53.7	0.10	-61.9	0.43	170.2
14.00	0.72	91.6	1.43	-61.5	0.09	-64.7	0.44	160.6
14.50	0.74	84.5	1.38	-69.0	0.09	-66.1	0.45	151.8
15.00	0.75	77.8	1.33	-76.3	0.09	-67.6	0.47	142.9
15.50	0.76	71.9	1.29	-83.5	0.09	-69.3	0.48	135.0
16.00	0.76	66.4	1.25	-90.6	0.09	-70.4	0.51	126.8
16.50	0.77	60.9	1.22	-97.9	0.09	-72.3	0.54	119.2
17.00	0.78	55.5	1.18	-105.2	0.09	-75.0	0.56	111.7
17.50	0.78	49.5	1.13	-112.6	0.09	-77.6	0.58	104.2
18.00	0.78	44.0	1.07	-119.8	0.09	-80.1	0.60	96.7
18.50	0.78	38.9	1.00	-126.3	0.09	-82.3	0.62	89.7
19.00	0.79	34.6	0.94	-132.5	0.09	-83.8	0.65	83.0
19.50	0.79	30.4	0.88	-138.1	0.09	-85.6	0.67	77.2
20.00	0.80	25.9	0.84	-143.7	0.09	-88.6	0.70	72.4

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Typical Common Source Scattering Parameters in the Ceramic Surface Mount Package (Cont'd)

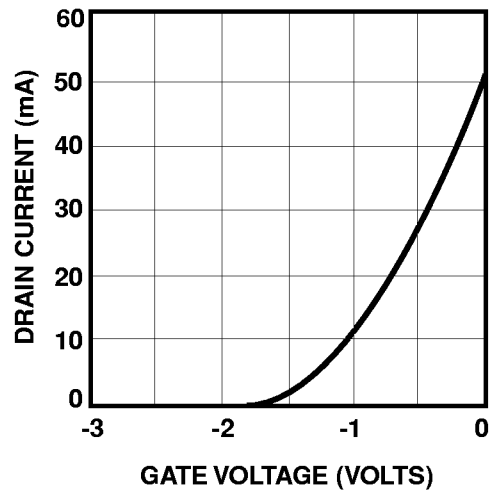
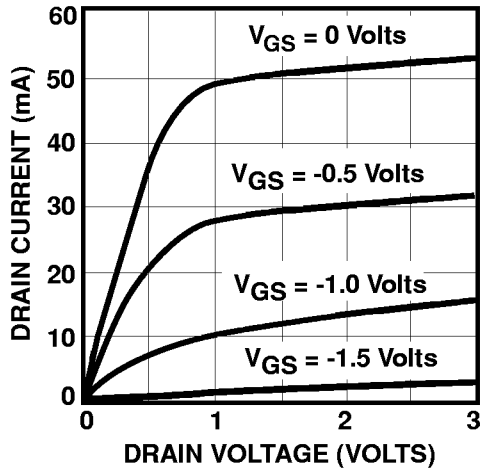
$V_{DS} = 3\text{ V}$, $I_{DS} = 30\text{ mA}$

Frequency (GHz)	S_{11E}		S_{21E}		S_{12E}		S_{22E}	
	Mag	Angle	Mag	Angle	Mag	Angle	Mag	Angle
0.50	1.02	-10.9	3.12	170.4	0.01	83.0	0.73	-6.3
1.00	1.01	-22.1	3.15	160.6	0.02	76.3	0.73	-12.7
1.50	1.01	-33.3	3.18	150.6	0.03	69.2	0.73	-19.8
2.00	0.95	-43.4	3.06	139.7	0.04	61.1	0.73	-25.7
2.50	0.93	-55.1	3.04	129.2	0.05	53.4	0.71	-32.3
3.00	0.90	-66.6	2.98	119.1	0.05	46.0	0.69	-39.0
3.50	0.88	-77.7	2.91	109.2	0.06	38.7	0.68	-45.5
4.00	0.85	-88.5	2.82	99.8	0.07	31.8	0.66	-51.3
4.50	0.82	-99.1	2.75	90.8	0.07	24.9	0.64	-56.8
5.00	0.79	-109.4	2.68	82.3	0.07	18.5	0.62	-61.8
5.50	0.76	-119.7	2.63	73.6	0.07	12.5	0.605	-67.0
6.00	0.74	-130.1	2.59	65.2	0.07	6.8	0.58	-72.0
6.50	0.71	-141.5	2.54	56.4	0.08	0.9	0.56	-78.0
7.00	0.68	-152.8	2.47	47.4	0.07	-5.7	0.53	-83.7
7.50	0.66	-163.3	2.40	39.3	0.07	-9.2	0.51	-88.6
8.00	0.65	-173.5	2.36	31.5	0.07	-10.3	0.50	-94.1
8.50	0.65	176.2	2.32	23.3	0.07	-10.7	0.49	-100.4
9.00	0.66	166.0	2.27	15.0	0.07	-13.5	0.48	-107.6
9.50	0.66	156.5	2.21	7.0	0.07	-16.1	0.47	-114.7
10.00	0.66	147.9	2.15	-0.6	0.07	-18.4	0.47	-121.8
10.50	0.67	138.9	2.09	-8.2	0.07	-20.9	0.46	-129.5
11.00	0.68	130.0	2.04	-16.0	0.08	-23.3	0.46	-137.2
11.50	0.69	121.1	1.98	-23.9	0.08	-25.3	0.45	-145.2
12.00	0.70	112.6	1.92	-31.9	0.08	-27.1	0.45	-153.6
12.50	0.71	104.3	1.85	-39.9	0.08	-28.8	0.44	-162.9
13.00	0.72	96.6	1.78	-47.8	0.08	-30.4	0.44	-172.6
13.50	0.74	89.1	1.71	-55.5	0.08	-31.7	0.44	177.3
14.00	0.75	82.0	1.64	-63.1	0.08	-33.7	0.44	167.4
14.50	0.76	75.5	1.58	-70.4	0.09	-35.2	0.45	158.4
15.00	0.77	69.1	1.52	-77.6	0.09	-37.4	0.47	149.2
15.50	0.79	63.5	1.48	-84.7	0.09	-40.0	0.49	141.0
16.00	0.79	58.4	1.44	-91.8	0.10	-43.0	0.52	132.5
16.50	0.80	53.0	1.40	-99.2	0.10	-46.1	0.54	124.6
17.00	0.81	47.7	1.35	-106.5	0.11	-49.8	0.56	116.7
17.50	0.81	41.9	1.30	-113.8	0.11	-53.6	0.59	109.0
18.00	0.81	36.6	1.23	-120.9	0.11	-57.7	0.61	101.0
18.50	0.81	31.8	1.15	-127.5	0.11	-61.0	0.63	93.6
19.00	0.81	27.7	1.08	-133.6	0.11	-63.9	0.65	86.6
19.50	0.82	23.7	1.02	-139.1	0.11	-67.3	0.68	80.4
20.00	0.82	19.5	0.97	-144.8	0.11	-71.1	0.070	75.2

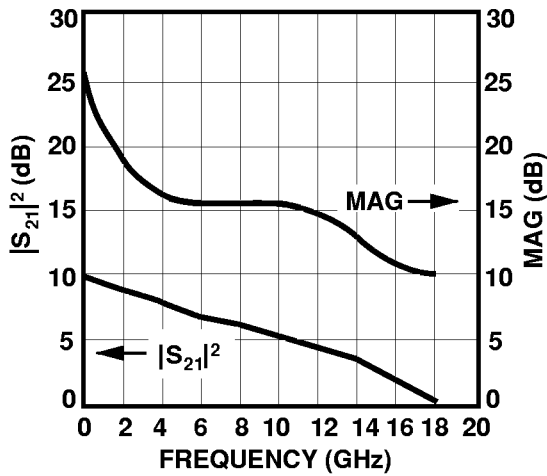
Specifications Subject to Change Without Notice.

Typical Performance Curves @ 25°C

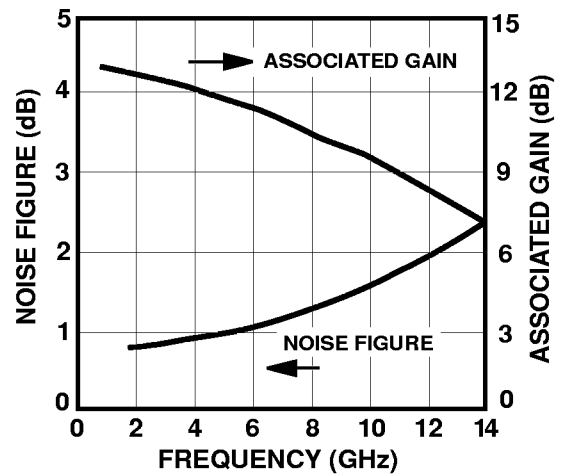
DRAIN CURRENT vs GATE VOLTAGE AT $V_{DS} = 3\text{ V}$



MAXIMUM AVAILABLE GAIN AND TRANSDUCER GAIN
 $V_{DS} = 3\text{ V}$, $I_{DS} = 30\text{ mA}$



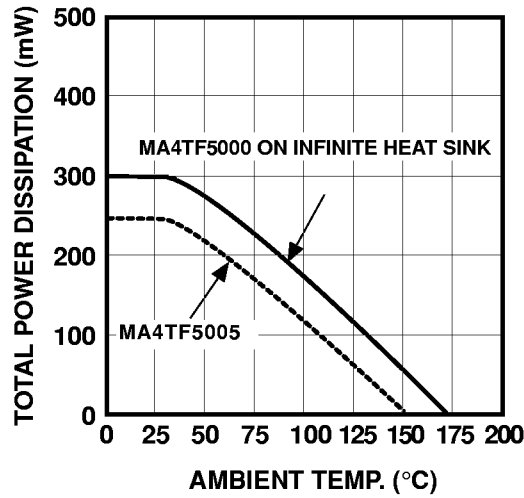
ASSOCIATED GAIN AND NOISE FIGURE vs FREQUENCY
 $V_{DS} = 3\text{ V}$, $I_{DS} = 30\text{ mA}$



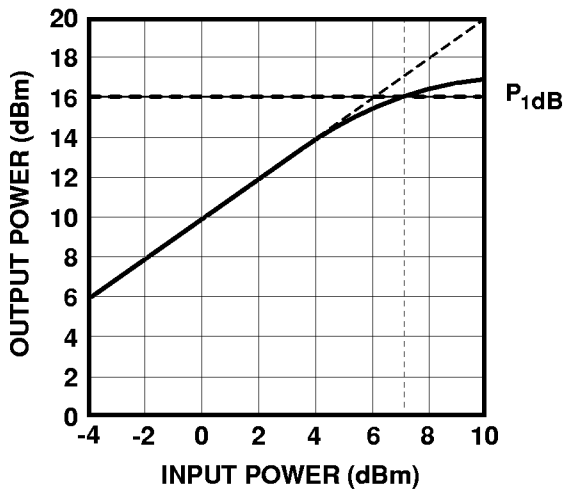
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Typical Performance Curves (Cont'd)

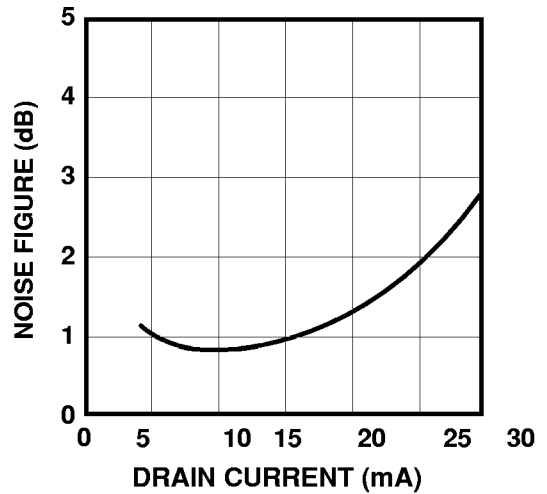
POWER DISSIPATION



OUTPUT POWER vs INPUT POWER
($P_{1dB} = 16 \text{ dBm}$)
 $V_{DS} = 3 \text{ V}$, $I_{DS} = 30 \text{ mA}$, $F = 4 \text{ GHz}$



NOISE FIGURE vs DRAIN CURRENT
 $V_{DS} = 3 \text{ V}$, $F = 4 \text{ GHz}$



Specifications Subject to Change Without Notice.

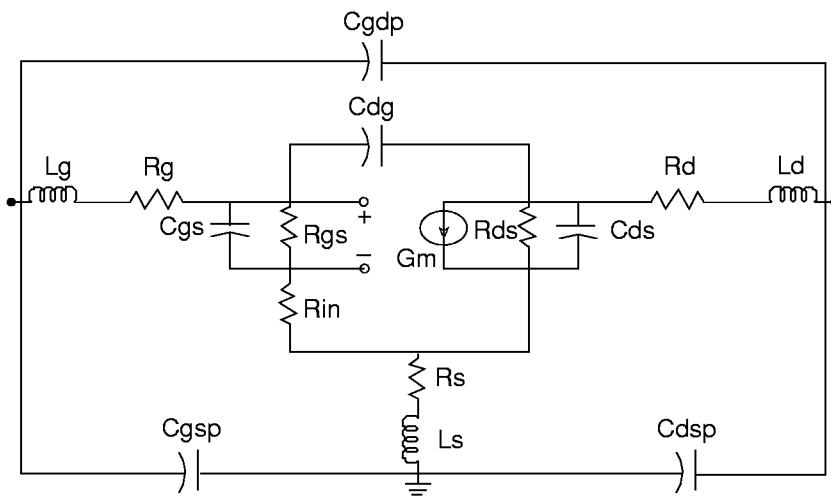
MA4TF5005 in the Ceramic Surface Mount Package
Typical Noise Parameters

$V_{DS} = 3V, I_{DS} = 10\text{ mA}$

Frequency (GHz)	NF_O (dB)	G_A (dB)	Γ_{OPT}		R_{η}
			Mag	Angle	
2.00	0.68	14.41	0.73	28.1	22.29
3.00	0.84	12.88	0.71	43.3	25.24
4.00	1.00	11.55	0.69	60.8	25.74
5.00	1.16	10.41	0.67	80.3	23.48
6.00	1.32	9.43	0.65	101.4	18.77
7.00	1.48	8.62	0.63	123.5	12.74
8.00	1.64	7.96	0.62	146.4	7.16
9.00	1.81	7.44	0.60	169.5	3.93
10.00	1.97	7.06	0.60	-167.5	4.61
11.00	2.13	6.81	0.60	-145.1	9.94
12.00	2.29	6.67	0.60	-123.7	19.75
13.00	2.45	6.65	0.61	-103.7	33.12
14.00	2.61	6.71	0.63	-85.6	48.79

MA4TF5005 in the Ceramic Surface Mount Package
Small Signal Model

$V_{DS} = 3V, I_{DS} = 10\text{ mA}$

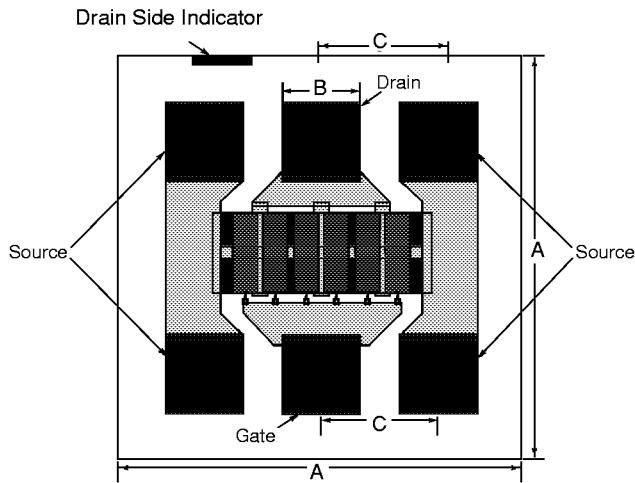


Element	Value
Rg	0.18 Ω
Rd	0.0015 Ω
Rs	5.5 Ω
Rin	5.0 Ω
Rgs	1481 Ω
Rds	406 Ω
Cgs	0.35 pF
Cds	0.16 pF
Cdg	0.055 pF

Element	Value
Gm	32 mS
Tau	8.62 ps
Lg	0.60 nH
Ld	0.59 nH
Ls	0.045 nH
Cgsp	0.065 pF
Cgdp	0.019 pF
Cdsp	0.039 pF

Specifications Subject to Change Without Notice.

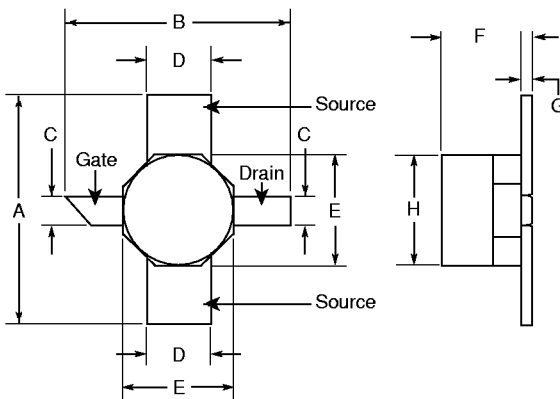
Chip – MA4TF5000
Case Style 1161



MA4TF5000

DIM.	INCHES (NOM.)	MILLIMETERS (NOM.)
A	0.016	0.406
B	0.002	0.050
C	0.003	0.075

Ceramic Surface Mount Package
Case Style 1105 — MA4TF5005



MA4TF5005

DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.150	0.165	3.80	4.20
B	0.150	0.165	3.80	4.20
C	0.014	0.026	0.35	0.65
D	0.032	0.047	0.80	1.20
E	0.063	0.079	1.60	2.00
F	—	0.057	—	1.45
G	0.002	0.008	0.05	0.20
H	0.063	0.079	1.60	2.00

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